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Advanced Etch Technology for Nanopatterning IV

Qinghuang Lin
Sebastian U. Engelmann
Editors

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The CID Number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages.

Contents

v	<i>Authors</i>
vii	<i>Conference Committee</i>
ix	<i>Introduction</i>

NANOPATTERNING FOR ADVANCED LOGIC AND MEMORY TECHNOLOGY NODES

9428 05	Etch patterning for advanced devices (Invited Paper) [9428-4]
9428 06	Challenges in High Aspect Ratio Contact (HARC) etching for DRAM capacitor formation (Invited Paper) [9428-5]
9428 07	Dry etch challenges for CD shrinkage in memory process (Invited Paper) [9428-6]

PLASMA AND RESIST INTERACTIONS, INCLUDING PATTERNING QUALITY CONTROL FOR LER, CD UNIFORMITY, ETC.

9428 09	Patterning in the era of atomic scale fidelity (Invited Paper) [9428-8]
9428 0A	Plasma etch challenges with new EUV lithography material introduction for patterning for MOL and BEOL [9428-9]
9428 0B	Spectral analysis of the line width and line edge roughness transfer during a self-aligned double patterning approach [9428-10]
9428 0C	H₂ plasma and neutral beam treatment of EUV photoresist [9428-11]

PATTERNING INTEGRATION SCHEMES: MULTILAYER PATTERNING, SELF-ALIGNED PATTERNING, ETC.

9428 0D	DSA planarization approach to solve pattern density issue (Invited Paper) [9428-12]
9428 0F	Trench and hole patterning with EUV resists using dual frequency Capacitively Coupled Plasma (CCP) [9428-14]
9428 0G	Challenges and mitigation strategies for resist trim etch in resist-mandrel based SAQP integration scheme [9428-15]

PATTERNING MATERIALS AND ETCH: JOINT SESSION WITH CONFERENCE 9425

9428 0H	Photoresist performance modification through plasma treatment (Invited Paper) [9428-16]
---------	--

9428 0I **Finding practical phenomenological models that include both photoresist behavior and etch process effects** [9428-17]

9428 0J **Molecular glass resist performance for nano-pattern transfer** [9428-18]

NEW PLASMA SOURCES AND NEW ETCHING TECHNOLOGIES

9428 0N **Low-temperature and damage-free transition metal and magnetic material etching using a new metallic complex reaction (Invited Paper)** [9428-21]

9428 0O **Electron energy distribution control by fiat: breaking from the conventional flux ratio scaling rules in etch (Invited Paper)** [9428-22]

EMERGING PATTERNING TECHNOLOGIES IN DSA AND OTHERS

9428 0S **RIE challenges for sub-15nm line-and-space patterning using directed self-assembly lithography with coordinated line epitaxy (COOL) process** [9428-26]

9428 0T **A facile route for fabricating graphene nanoribbon array transistors using graphoepitaxy of a symmetric block copolymer** [9428-27]

POSTER SESSION

9428 0V **Direct comparison of the performance of commonly used e-beam resists during nano-scale plasma etching of Si, SiO₂, and Cr** [9428-29]

9428 0W **A way to integrate multiple block layers for middle of line contact patterning** [9428-31]

9428 0X **Synchronous pulsing plasma utilization in dummy poly gate removal process** [9428-33]

9428 0Y **Characterization of the effect of etch process operating environments on the perfluoroelastomer chamber seal systems** [9428-34]

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Altamirano-Sánchez, E., 0C	Jung, Taewoo, 06
Argoud, M., 0D	Kamarthy, Gowri, 09
Arnold, John, 0A, 0F	Kanai, H., 0S
Arnold, Michael S., 0T	Kanarik, Keren J., 09
Azuma, T., 0S	Kasahara, Y., 0S
Barnola, S., 0B, 0D	Kawamonzen, Y., 0S
Beique, Genevieve, 0A, 0F	Kihara, N., 0S
Biolsi, Peter, 0G	Kim, Myungwoong, 0T
Boemmels, J., 0W	Kim, Yongjin, 06
Boettcher, Monika, 0V	Kimura, Yoshie, 09
Bos, S., 0D	Ko, Akiteru, 0G
Braithwaite, N. St. J., 0C	Kobayashi, K., 0S
Broui, M., 0W	Kodera, K., 0S
Chevalier, X., 0D	Koike, Kyohei, 0H
Chiba, Yuki, 0F	Kolb, Tristan, 0J
Choi, Jonathan W., 0T	Kubota, H., 0S
Claveau, G., 0D	Kubota, Shinji, 0N
Cooke, Mike, 0V	Kubota, Tomihiro, 0N
Darnon, M., 0B	Kumar, Kaushik, 0F, 0G
Das, Sanjana, 0G	Kunnen, E., 0W
De Gendt, S., 0C	Kwak, Nohjung, 06
de Marneffe, Jean-François, 0C, 0J	Kyoh, Suigen, 07
Demuynck, S., 0W	Labelle, Catherine, 0A, 0F
De Schepper, P., 0C	Labonte, Andre, 0A, 0F
DeVillers, Anton, 0G	Lapeyre, C., 0D
Do, Thuy, 0I	Lee, Byoungseok, 06
Dupuy, E., 0B	Lee, Changwoo, 0A
el Otell, Ziad, 0C, 0J	Lee, Sangdo, 06
Farrell, Richard, 0G	Leobandung, E., 05
Feurprier, Yannick, 0F	Lill, Thorsten, 09
Fouchier, M., 0B	Liu, Chinchao, 0Y
Franke, Elliott, 0G	Liu, Eric, 0G
Friddle, Phil, 0A	Lutker-Lee, Katie, 0F
Gharbi, A., 0D	Marinov, D., 0C
Goodyear, Andy, 0V	Marks, Jeffrey, 09
Gopalan, Padma, 0T	Matsumoto, Hiroie, 0F
Goss, Michael, 0A	Matsumoto, Takanori, 07
Gottscho, Richard A., 09	Matsushita, Takaya, 07
Grampeix, H., 0B	Meng, Xiao-Ying, 0X
Hamieh, Bassem, 0A, 0F	Metz, Andrew, 0F
Han, Eunghak, 0T	Mignot, Yann, 0A, 0F
Han, Qiu-Hua, 0X	Minegishi, S., 0S
Hansel, Leander, 0J	Miyagi, K., 0S
Hara, Arisa, 0H	Miyama, Ryo, 0N
Hashimoto, Kohji, 07	Mohanty, Nihar, 0G
Huang, Ruixuan, 0X	Monget, C., 0D
Ito, Kiyohito, 0G	Moyama, Kazuki, 0N
Joubert, O., 0B	Mucci, John, 0A
Jung, Sunwook, 0I	Mukai, Hidefumi, 07

Nagabhirava, Bhaskar, 0A
 Natori, Sakurako, 0H
 Navarro, C., 0D
 Nawa, Kenjiro, 0G
 Neuber, Christian, 0J
 Nicolet, C., 0D
 Nomura, S., 0S
 Nozawa, Toshihisa, 0N
 Okabe, Noriaki, 0H
 O'Meara, Dave, 0G
 Oyama, Kenichi, 0H
 Pargon, E., 0B
 Park, Sungki, 06
 Pimenta-Barros, P., 0B, 0D
 Posseme, N., 0D
 Pradelles, J., 0B
 Raley, Angelique, 0G
 Ranjan, Alok, 0G, 0O
 Rassoul, Nouradine, 0A
 Rastogi, Vinayak, 0F
 Reichl, Gary, 0Y
 Ringk, Andreas, 0J
 Ryckaert, J., 0W
 Safron, Nathaniel S., 0T
 Samukawa, Seiji, 0N
 Sarrazin, A., 0D
 Sato, H., 0S
 Scheer, Steven, 0G
 Schmitz, Stefan, 0A
 Seino, Y., 0S
 Servin, I., 0D
 Shen, Meihua, 09
 Sherpa, Sonam, 0O
 Shiraishi, M., 0S
 Smith, Jeffrey, 0G
 Stolberg, Ines, 0V
 Sturtevant, John, 0I
 Tallaron, C., 0D
 Tan, Samantha, 09
 Tiron, R., 0D
 Tobana, T., 0S
 Vahedi, Vahid, 09
 Ventzek, Peter, 0O
 Versluijs, J., 0W
 Wang, Mingmei, 0G, 0O
 Wang, Peng, 0A
 Wu, Jian, 0A
 Yaegashi, Hidetami, 0H
 Yamato, Masatoshi, 0H
 Yamauchi, Shohei, 0H
 Yang, Richard, 0A
 Zhang, Hai-Yang, 0X

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- 1 Overviews of Nanopatterning Challenges
Catherine Labelle, GLOBALFOUNDRIES, Inc. (United States)
Rich Wise, Lam Research Corporation (United States)

- 2 Nanopatterning for Advanced Logic and Memory Technology Nodes
Sang-Hoon Cho, SK Hynix, Inc. (Korea, Republic of)
Eric A. Hudson, Lam Research Corporation (United States)
Robert Turkot, Intel Corporation (United States)

- 3 Plasma and Resist Interactions, including Patterning Quality Control for LER, CD Uniformity, etc.
Erwine Pargon, LTM CNRS (France)
Sebastian U. Engelmann, IBM Thomas J. Watson Research Center (United States)

- 4 Patterning Integration Schemes: Multilayer Patterning, Self-Aligned Patterning, etc.
Nicolas Posseme, CEA-LETI (France)
Erwine Pargon, LTM CNRS (France)

- 5 Patterning Materials and Etch: Joint Session with Conferences 9425 and 9428
Qinghuang Lin, IBM Thomas J. Watson Research Center (United States)
Thomas I. Wallow, Brion Technologies, Inc. (United States)

- 6 Materials and Etch in Emerging Technologies: Joint Session with Conferences 9425 and 9428
Christoph K. Hohle, Fraunhofer Institute for Photonic Microsystems (Germany)
Qinghuang Lin, IBM Thomas J. Watson Research Center (United States)

- 7 New Plasma Sources and New Etching Technologies
Seiji Samukawa, Tohoku University (Japan)
Nicolas Posseme, CEA-LETI (France)
Julie Bannister, Tokyo Electron America, Inc. (United States)

- 8 Emerging Patterning Technologies in DSA and Others
Ying Zhang, Applied Materials, Inc. (United States)
Ricardo Ruiz, HGST (United States)

Introduction

This proceedings volume features accepted papers from the SPIE Conference on Advanced Etch Technology for Nanopatterning IV (The SPIE Etch Conference) held as part of the International Symposium on Advanced Lithography, 22–26 February 2015 in San Jose, California. These proceedings papers cover the latest advances in the wide field of etch and nanopatterning technology and offer a glimpse of the state of the art of this important field of semiconductor technology.

This year's conference continued the fine tradition of wide international representation and attracted many researcher from related fields. For the first time, our conference lasted two full days and was divided into eight sessions, all of which continued to garner tremendous interest among conference attendees.

- Overview of Nanopatterning Challenges
- Nanopatterning for Advanced Logic and Memory Technology Nodes
- Plasma and Resist Interactions, including Patterning Quality Control for LER, CD Uniformity, etc.
- Paterning Integration Schemes: Multilayer Patterning, Self-Aligned Patterning, etc.
- Patterning Materials and Etch: Joint Session with Conference 9425
- Materials and Etch in Emerging Technologies: Joint Session with Conference 9425
- New Plasma Sources and New Etching Technologies
- Emerging Patterning Technologies in DSA and Others

This year, the conference hosted two well-attended joint sessions on Patterning Materials and Etch as well as Materials and Etch in Emerging Technologies with the Advances in Patterning Materials and Processes Conference. The Overview Session, where some of the most important fundamental issues being faced in the world of nanopatterning and etch were discussed, drew very big crowds.

We hope that this proceedings volume will prove valuable to the many patterning scientists and engineers working in the fast-moving semiconductor industry. We also hope that it will serve as a useful reference for those who are interested in nanofabrication, micro- and nano-fluidics, micro- and nano-photonics, Micro-Electro-Mechanical Systems (MEMS), BioMEMS, organic electronics, advanced packaging, as well as bio-chips.

We thank the authors, particularly the invited speakers, for their valuable contributions to this conference and this proceedings volume. The SPIE Etch Conference is highly regarded among the worldwide patterning community due to the high quality of presentations and proceedings papers.

We also thank members of the organizing committee for their dedication and hard work to ensure the high quality of this conference. We are also grateful to LAM Research Corporation for their generous financial support. Finally, we extend our sincere thanks to the SPIE staff for their tireless efforts and their meticulous organizational skills in assembling and publishing this proceedings volume and helping make this year's SPIE Etch Conference a success.

Qinghuang Lin
Sebastian U. Engelmann